

Request For Quotation

Order the parts you need from our real-time inventory database. Simply complete a request for quotation form with your part information and a sales representative will respond to you with price and availability.

Request For Quotation

Your free datasheet starts on the next page.

More datasheets and data books are available from our homepage: http://www.datasheetarchive.com



BD439/BD440 BD441/BD442

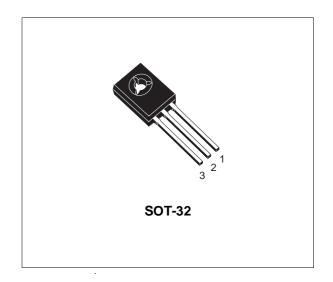
COMPLEMENTARY SILICON POWER TRANSISTORS

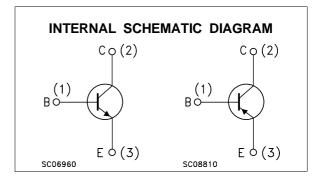
- SGS-THOMSON PREFERRED SALESTYPES
- COMPLEMENTARY PNP NPN DEVICES

DESCRIPTION

The BD439 and BD441 are silicon epitaxial-base NPN power transistors in Jedec SOT-32 plastic package, intented for use in power linear and switching applications.

The complementary PNP types are BD440, and BD442 respectively.





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit
		NPN	BD439	BD441	
		PNP	BD440	BD442	
V _{CBO}	Collector-Base Voltage (I _E = 0)		60	80	V
V _{CES}	Collector-Emitter Voltage (V _{BE} = 0)		60	80	V
V_{CEO}	Collector-Emitter Voltage (I _B = 0)		60	80	V
V _{EBO}	Emitter-Base Voltage (I _C = 0)			5	V
Ic	Collector Current		4		Α
I _{CM}	Collector Peak Current (t ≤ 10 ms)		7		Α
lΒ	Base Current		1		Α
P _{tot}	Total Dissipation at T _c ≤ 25 °C	36		W	
T _{stg}	Storage Temperature		-65 to 150		°C
Tj	Max. Operating Junction Temperature		15	°C	

For PNP types voltage and current values are negative.

May 1997 1/4

THERMAL DATA

R _{thj-case}	Thermal Resistance Junction-case	Max	3.5	°C/W
$R_{thj-amb}$	Thermal Resistance Junction-ambient	Max	100	°C/W

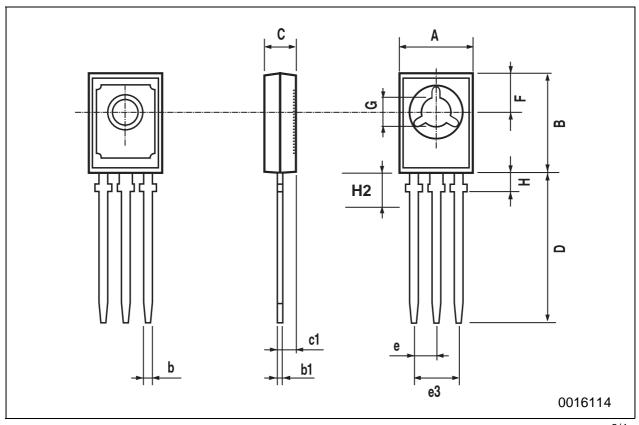
ELECTRICAL CHARACTERISTICS ($T_{case} = 25$ $^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _E = 0)	for BD439/440 for BD441/442	05			100 100	μA μA
Ices	Collector Cut-off Current (V _{BE} = 0)	for BD439/440 for BD441/442	05			100 100	μA μA
I _{EBO}	Emitter Cut-off Current (I _C = 0)	V _{EB} = 5 V				1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 100 mA	for DB439/440 for BD441/442	60 80			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = 2 A	$I_B = 0.2 A$			0.8	V
V _{BE} *	Base-Emitter Voltage	I _C = 10 mA I _C = 2 A	$V_{CE} = 5 V$ $V_{CE} = 1 V$		0.58	1.5	V
h _{FE} *	DC Current Gain	$I_C = 10 \text{ mA}$ $I_C = 500 \text{ mA}$ $I_C = 2 \text{ A}$	V _{CE} = 5 V for BD439/440 for BD441/442 V _{CE} = 1 V for BD439/440 for BD441/442 V _{CE} = 1 V for BD439/440 for BD441/442	20 15 40 40 25 15	130 130 140 140		
h _{FE1} /h _{FE2} *	Matched Pair	IC = 500 mA	V _{CE} = 1 V			1.4	
f _T	Transition frequency	I _C = 250 mA	V _{CE} = 1 V	3			MHz

^{*} Pulsed: Pulse duration = 300 μs, duty cycle 1.5 %

SOT-32 (TO-126) MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α	7.4		7.8	0.291		0.307
В	10.5		10.8	0.413		0.445
b	0.7		0.9	0.028		0.035
b1	0.49		0.75	0.019		0.030
С	2.4		2.7	0.040		0.106
c1	1.0		1.3	0.039		0.050
D	15.4		16.0	0.606		0.629
е		2.2			0.087	
e3	4.15		4.65	0.163		0.183
F		3.8			0.150	
G	3		3.2	0.118		0.126
Н			2.54			0.100
H2		2.15			0.084	



Information furnished is believed to be accurate and reliable. However, SGS-THOMSON Microelectronics assumes no responsability for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may results from its use. No license is granted by implication or otherwise under any patent or patent rights of SGS-THOMSON Microelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. SGS-THOMSON Microelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of SGS-THOMSON Microelectonics.

© 1997 SGS-THOMSON Microelectronics - Printed in Italy - All Rights Reserved

SGS-THOMSON Microelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Hong Kong - Italy - Japan - Korea - Malaysia - Malta - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A

